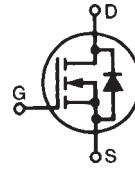


Polar™ Power MOSFET

HiPerFET™

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFN20N120P

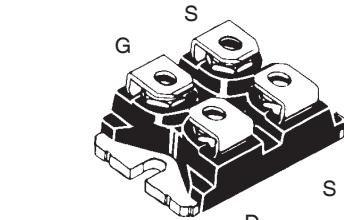


V_{DSS} = 1200V
I_{D25} = 20A
R_{DS(on)} ≤ 570mΩ
t_{rr} ≤ 300ns

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	1200	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	1200	V
V _{GSS}	Continuous	± 30	V
V _{GSM}	Transient	± 40	V
I _{D25}	T _C = 25°C	20	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	50	A
I _A	T _C = 25°C	10	A
E _{AS}	T _C = 25°C	1	J
dV/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	20	V/ns
P _D	T _C = 25°C	595	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6mm (0.062 in.) from case for 10s	300	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1mA	t = 1min t = 1s	V~ V~
M _d	Mounting torque Terminal connection torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 1mA	1200		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1mA	3.5		V
I _{GSS}	V _{GS} = ± 30V, V _{DS} = 0V		± 200	nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0V	T _J = 125°C	25 5	μA mA
R _{DS(on)}	V _{GS} = 10V, I _D = 10A, Note 1		570	mΩ

miniBLOC, SOT-227 B (IXFN)



G = Gate D = Drain
S = Source

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Applications:

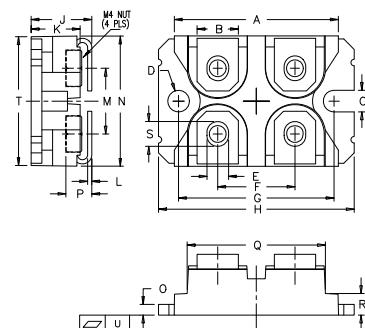
- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20V, I _D = 10A, Note 1	10	16	S
C_{iss} C_{oss} C_{rss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	11.1	nF	
		600	pF	
		60	pF	
R_{Gi}	Gate input resistance	1.60	Ω	
t_{d(on)} t_r t_{d(off)} t_f	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 10A R _G = 1Ω (External)	49	ns	
		45	ns	
		72	ns	
		70	ns	
Q_{g(on)} Q_{gs} Q_{gd}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 10A	193	nc	
		74	nc	
		85	nc	
R_{thJC}			0.21	°C/W
R_{thCS}		0.05		°C/W

Source-Drain DiodeT_J = 25°C unless otherwise specified)

		Characteristic Values		
		Min.	Typ.	Max.
I_s	V _{GS} = 0V		20	A
I_{SM}	Repetitive, pulse width limited by T _{JM}		80	A
V_{SD}	I _F = I _S , V _{GS} = 0V, Note 1		1.5	V
t_r Q_{RM} I_{RM}	I _F = 10A, -di/dt = 100A/μs V _R = 100V		300	ns
		0.84		μC
		9		A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

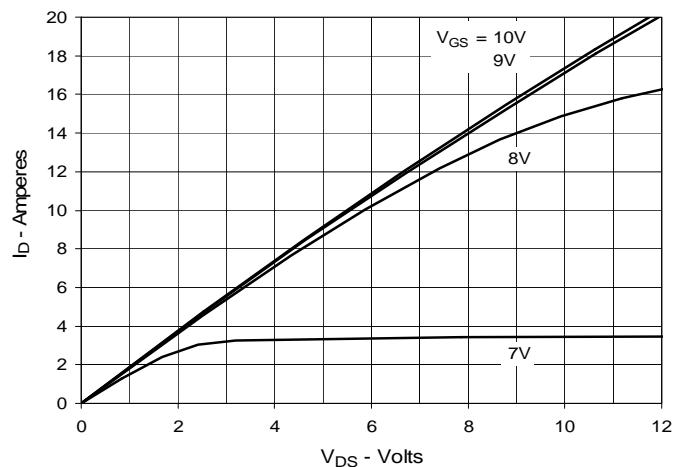
SOT-227B Outline

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

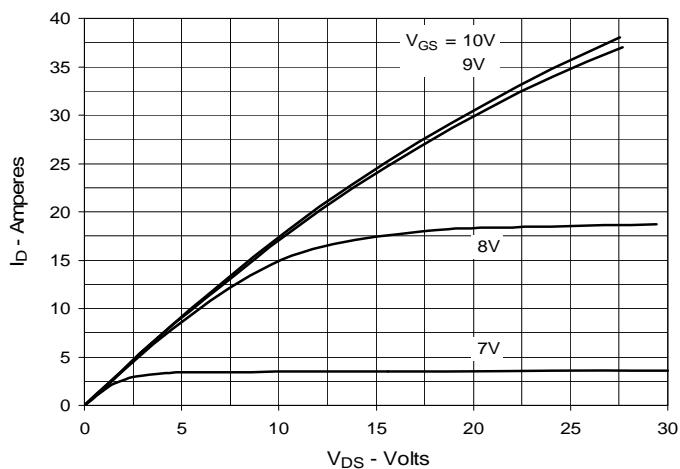
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

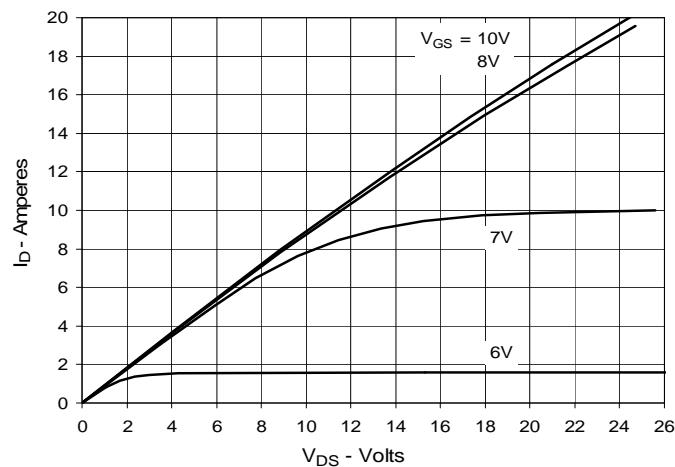
**Fig. 1. Output Characteristics
@ 25°C**



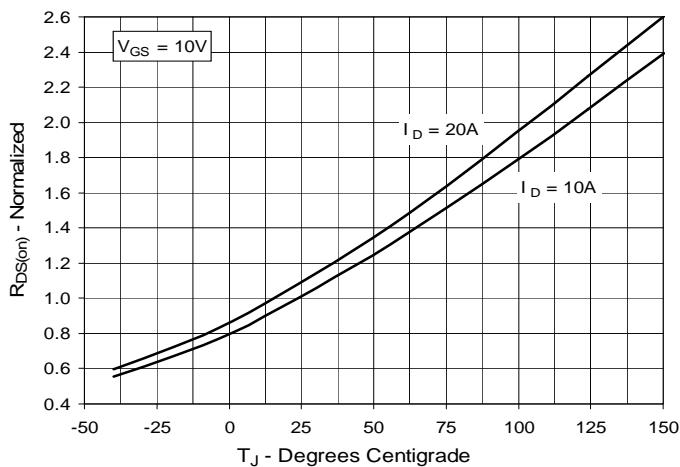
**Fig. 2. Extended Output Characteristics
@ 25°C**



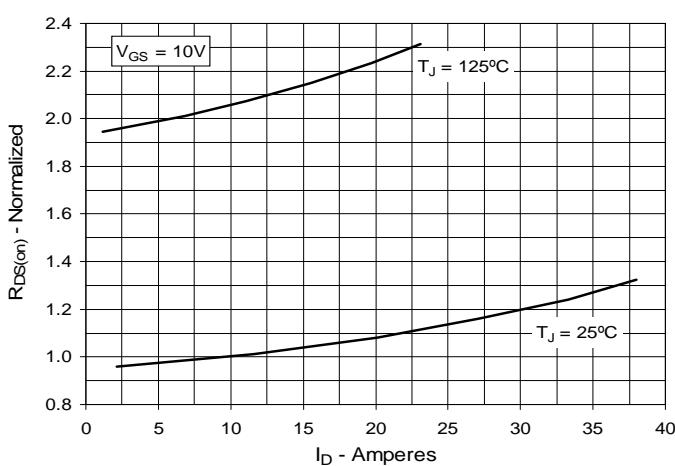
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 10A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 10A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

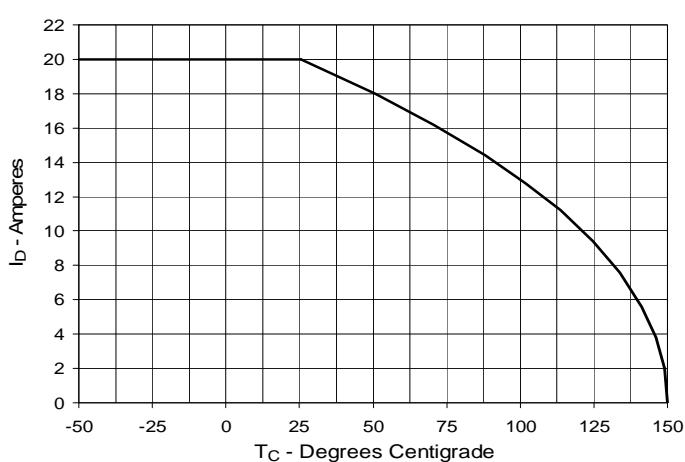
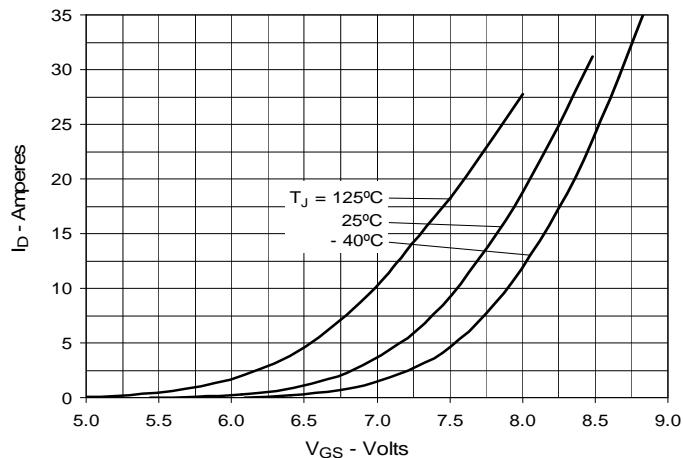
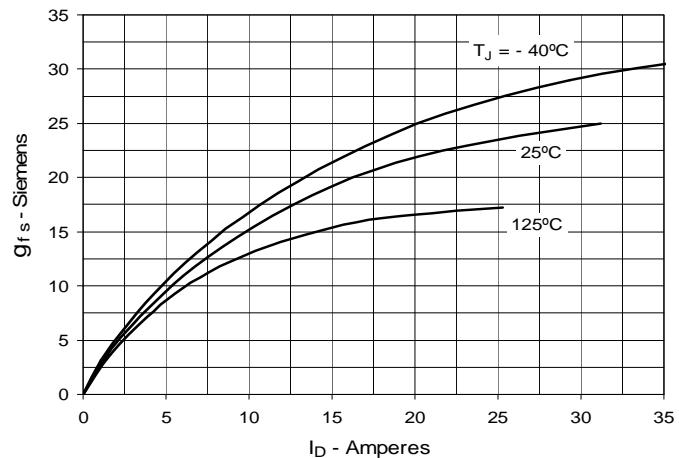
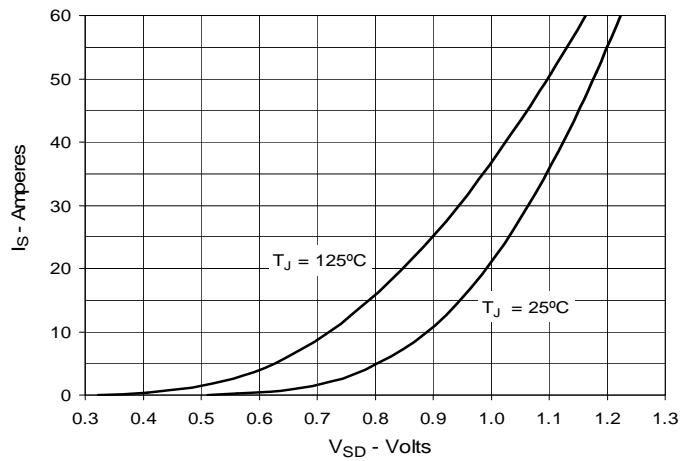
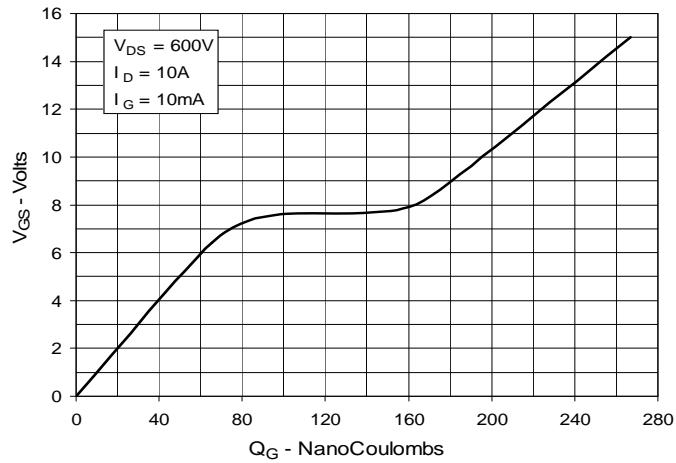
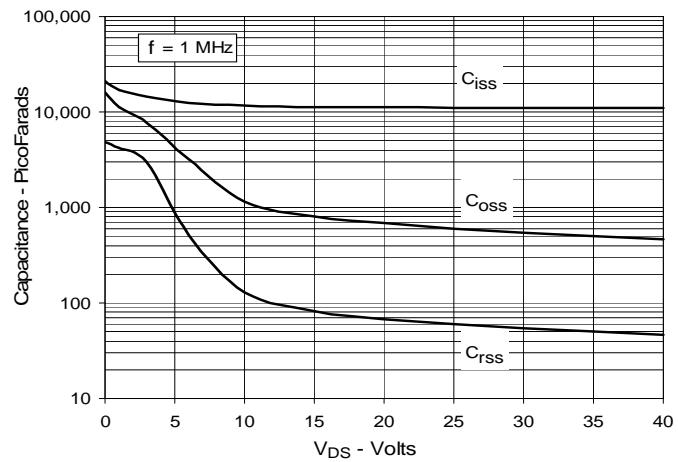
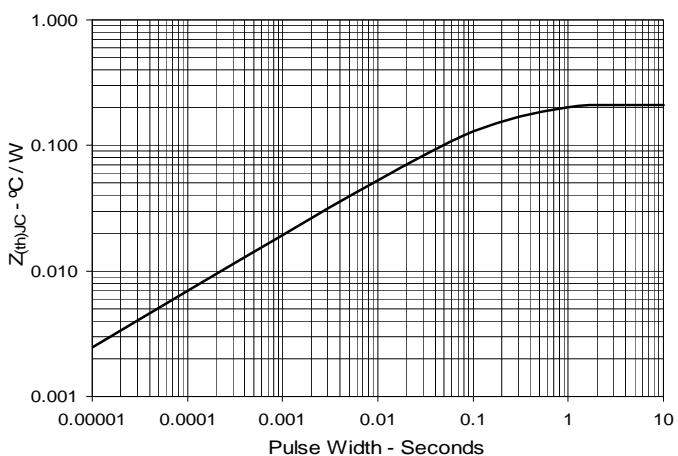


Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Maximum Transient Thermal Impedance**



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